

Mayer, Fortkort & Williams, PC  
251 North Avenue West. 2<sup>nd</sup> Floor  
Westfield, NJ 07090

---

## Fax Cover Sheet

DATE:	July 2, 2003	PAGES:	<u>10 (ten) w/cover</u>
TO:	Examiner Tan N. Tran GAU 2826	PHONE:	(703) 305-3362
		FAX:	(703) 872-9319
FROM:	Karin L. Williams Mayer, Fortkort & Williams, PC	PHONE:	(908) 518-7700
		FAX:	(908) 518-7795

---

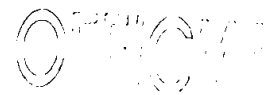
### Message

DOCKET GS 150

Please see attached: Response After Final Rejection

RECEIVED  
CENTRAL FAX CENTER

OCT 23 2003



---

***Response after Final Rejection***  
***Expedited Handling Requested - GAU 2826***

---

---

### CONFIDENTIALITY NOTICE

This facsimile transmission is intended only for the use of the addressee and may contain confidential information which is protected by the attorney/client privilege. If you are not the recipient, you are hereby notified that any disclosure, copying, distribution or the taking of any action in reliance on the contents of this information is strictly prohibited. If you have received this communication in error, please notify us immediately by telephone to arrange for its return.

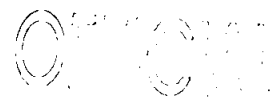
Patent  
10/010,484

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Hshieh et al.  
Serial No.: 10/010,484  
Filed: November 20, 2001  
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure  
Art Unit: 2826  
Examiner: Tan N. Tran  
Docket No.: GS 150

**RECEIVED**  
CENTRAL FAX CENTER  
OCT 23 2003

Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450



**RESPONSE AFTER FINAL REJECTION**

Sir:

In response to the second final Office Action dated July 23, 2003 (Paper No. 12), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.